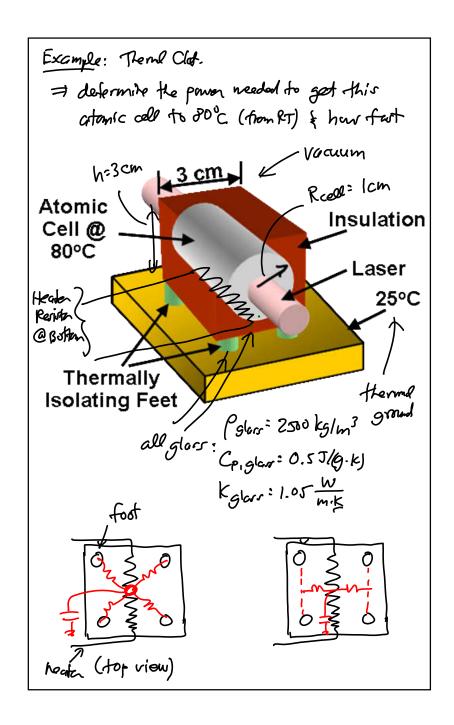
## EE C247B/ME C218: Introduction to MEMS Design

## <u>Lecture 5w</u>: Benefits of Scaling III

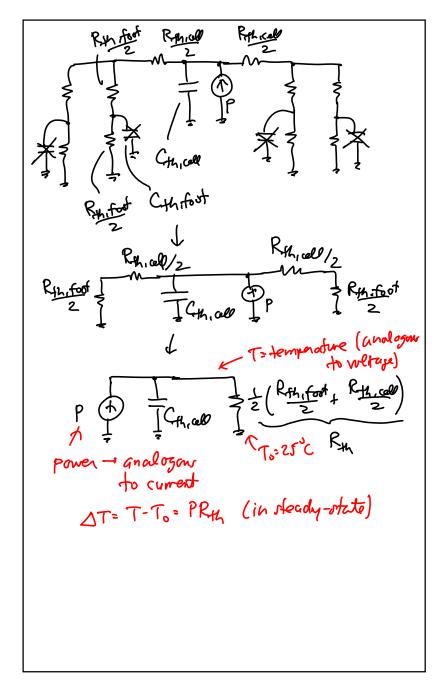
## <u>Lecture 5</u>: Benefits of Scaling III

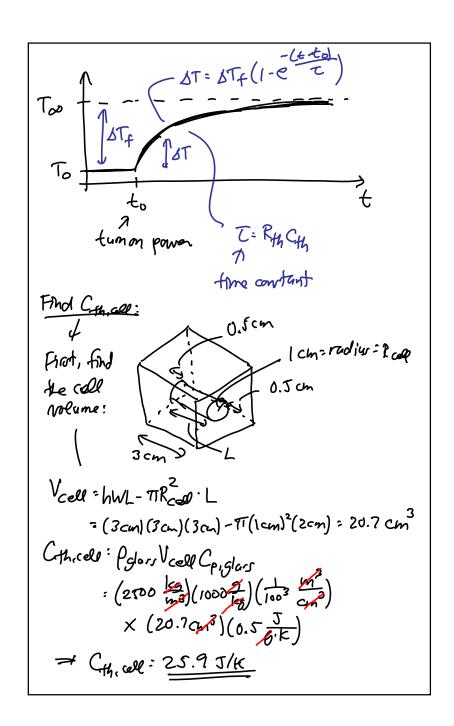
- · Announcements:
- HW#1 due this coming Thursday at 10 a.m. in the EE247B/ME218 Homework box near 140 Cory
- Hopefully, you've watched the video lectures from last week; otherwise, you'll have a hard time understanding this lecture
- -----
- · Today:
- · Reading: Senturia, Chapter 1
- · Lecture Topics:
  - **♦** Benefits of Miniaturization
  - **Sexamples** 
    - -GHz micromechanical resonators
    - -Chip-scale atomic clock
    - -Thermal Circuits
    - -Micro gas chromatograph
- · Probably won't get to it, but next up is:
- · Senturia, Chpt. 3; Jaeger, Chpt. 2, 3, 6
- Servicial, Shipt. 3, Gaeger, Chipt. 2, 3, 6
  - **\$ Photolithography**
  - **⇔** Etching
  - **♥** Oxidation

  - ♥ Ion Implantation
  - **♦** Diffusion
- -----
- <u>Last Time</u>: Thermal circuit modeling

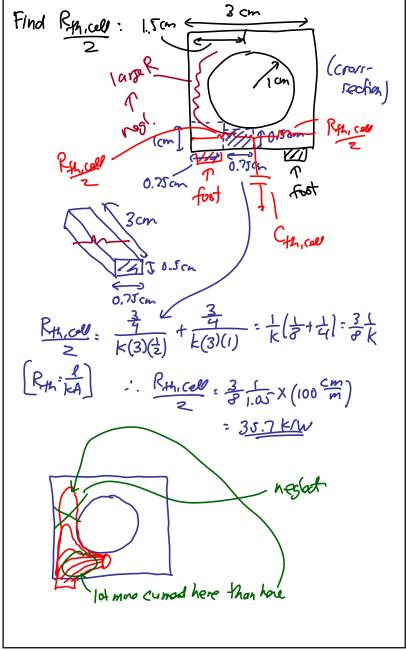


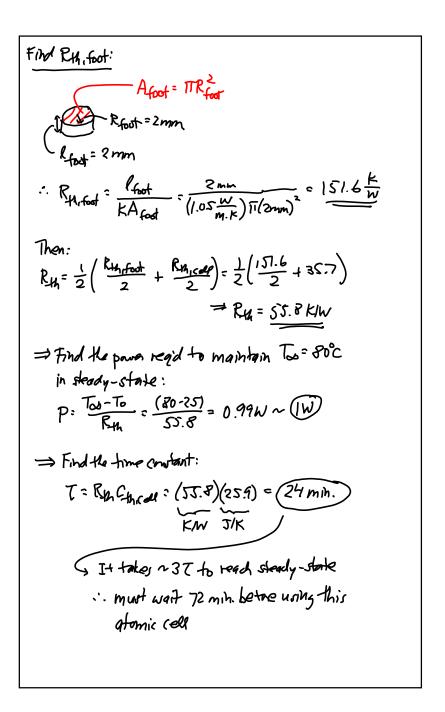
<u>Lecture 5w</u>: Benefits of Scaling III

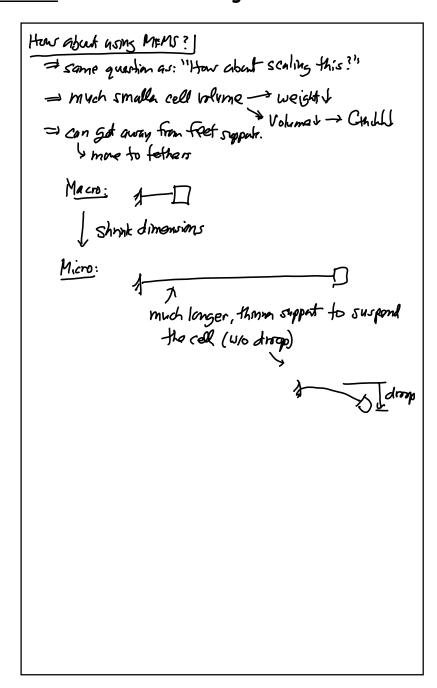


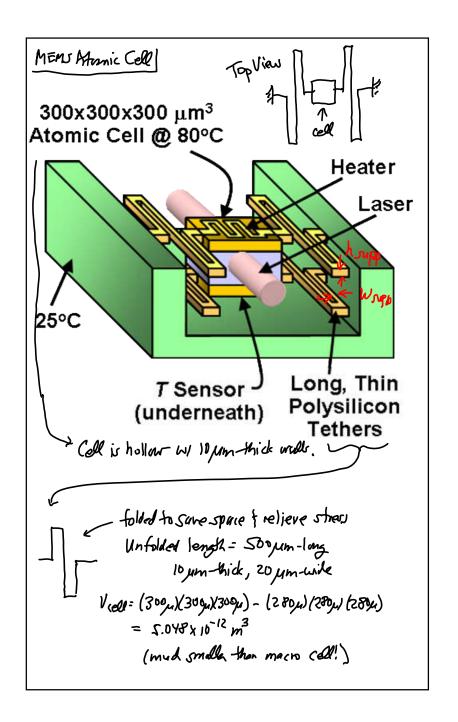


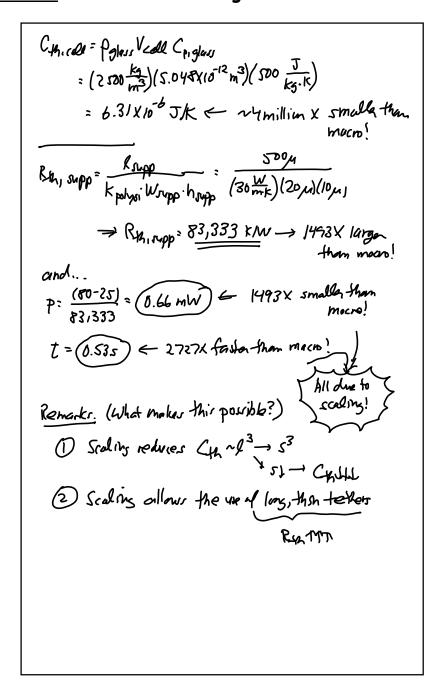
Lecture 5w: Benefits of Scaling III Find Ryn, cell: 1.500 (Cross- $\frac{\sum_{k,ou} \frac{3}{4}}{\sum_{k} \frac{3}{(3)(1)}} + \frac{3}{k} \frac{1}{(3)(1)} = \frac{1}{k} \left(\frac{1}{2} + \frac{1}{4}\right) = \frac{3}{2} \frac{1}{k}$ [RH: RA] : RHICED: 3 IN X (100 CM) = 35.7 K/W

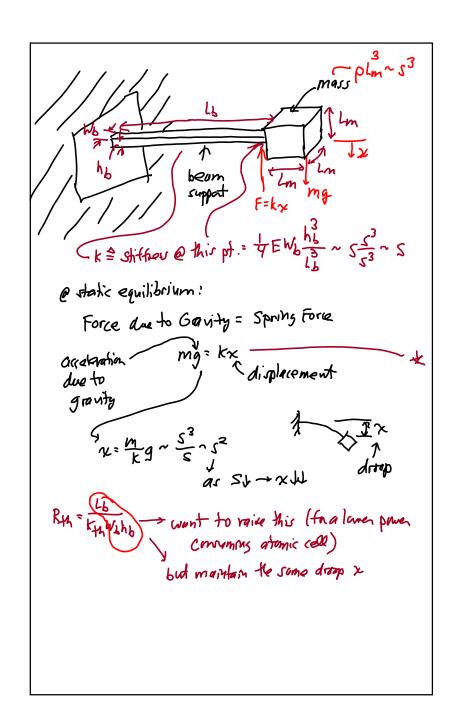












\* 
$$\rho l_{m} g = \frac{1}{4} E W_{b} \frac{h_{b}^{3}}{l_{b}^{3}} \chi$$

$$\frac{l_{b}}{W_{b}h_{b}} = \frac{1}{4} E \frac{h_{b}^{2}}{l_{b}^{2}} \chi \frac{1}{\rho l_{m} g} \sim \frac{s^{2}}{s^{2}} \frac{1}{s^{3}} \sim \frac{1}{s^{3}}$$

$$\sim R_{h}$$

$$4 as SI \rightarrow \frac{l_{b}}{W_{b}h_{b}} \sim R_{h} MM$$

 Go through slides 30-31 and 37-48 in Module 2 to finish up Thermal Circuits and cover Micro Gas Analyzers